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McDonnell Boehnen Hulbert & Berghoff LLP 300 South Wacker Drive Chicago, Illinois 60606 Telephone: (312) 913-0001 Facsimile: (312) 913-0002

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Honeywell Ref. No. H0002270 DIV

MBHB Case No. 06-308-E

Serial No.

10/764,938

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Applicant: Fathimulla et al.

Filing Date: January 26, 2004

Group: 2814

## **U.S. PATENT DOCUMENTS**

Examiner Initial	No.	Document Number	Date	Name	Class	Subclass	Filing Date

## FOREIGN PATENT DOCUMENTS

Examiner Initial	No.	Document Number	Date	Country	Class	Subclass	<u>Translation</u> Yes No
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	1.	A.B Glaser et al., "Integrated Circuit Engineering," p. 265-267, 289 Addison-Wesley, 1977
	2.	U.S. Davidsohn and F. Lee., "Dielectric-Isolated Integrated-Circuit Substrate Processes." Proc. IEEE 57: 1532-1537 (September 1969).